



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16760Generic Copy

Issue Date: 09-Nov-2011**TITLE:** Product Transfer from HANA to Seremban for 6L TSOP**PROPOSED FIRST SHIP DATE:** 09-Feb-2012 or upon customer's approval**AFFECTED CHANGE CATEGORY(S):** On Semiconductor Assembly/Test Site**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**Contact your local ON Semiconductor Sales Office or Raj Uppala<raj.uppala@onsemi.com>**SAMPLES:** Contact your local ON Semiconductor Sales Office or Raj Uppala
<raj.uppala@onsemi.com>**ADDITIONAL RELIABILITY DATA:** AvailableContact your local ON Semiconductor Sales Office or Lakshmi Kari<Lakshmi.Kari@onsemi.com>**NOTIFICATION TYPE:**

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.**DESCRIPTION AND PURPOSE:**

This Process Change Notice is to notify customers of the Transfer of assembly/test site from HANA, Thailand to ON Semiconductor's, Seremban Malaysia facility.

The devices listed on this FPCN have historically been assembled / tested at the HANA located in Thailand.

Due to flooding in Thailand, the assembly/test site in Hana, Thailand is no longer operational.

Moving forward, these devices will be processed at ON Semiconductor's, Seremban Malaysia facility.

There will be no changes in device functionality. Reliability will continue to meet or exceed ON Semiconductor's highest standards.



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RELIABILITY DATA SUMMARY:

Reliability Test Results:

Device Description:

Device	NUP4302MR6T1G	Wafer Fab Site	ON ISMF	Seremban, Malaysia
Package	TSOP6	Assembly Site	ON SBN	Seremban, Malaysia
MSL Level	MSL 1 @ 260	Final Test Site	ON SBN	Seremban, Malaysia
Technology	Zener	S06607		
Final Lead Finish	100% Matte Sn	Package Code	0680	

#	Test	Name	Test Conditions	End Point Req's	Test Results	(rej/ ss)	(rej/ ss)	(rej/ ss)	(rej/ ss)
					Read Point	Lot A	Lot B	Lot C	Lot D
1	Prep	Sample preparation and initial part testing	various	---	Initial Electrical	done	done	done	done
	HTRB	High Temp Reverse Bias	TA = 150°C for 1008 hours	c = 0, Room	Initial	0/80	0/80	0/80	0/80
					504 Hrs	0/80	0/80	0/80	0/80
					1008 Hrs	0/80	0/80	0/80	0/80
	PC	MSL 1 Preconditioning	IR @ 260 °C	c = 0, Room					
	IOL-PC	Intermittent OL-PC	Ta=+25°C, delta Tj=100°C On/off = 2 min	c = 0, Room	Post PC Electrical	0/80	0/80	0/80	0/80
					7500 cyc	0/80	0/80	0/80	0/80
					15000 cyc	0/80	0/80	0/80	0/80
	TC-PC	Temperature Cycling - PC		c = 0, Room	Post PC Electrical	0/80	0/80	0/80	0/80
					500 Cyc	0/80	0/80	0/80	0/80
					1000 Cyc	0/80	0/80	0/80	0/80
	AC-PC	Autoclave-PC	121°C/100% RH/15psig	c = 0, Room	Post PC Electrical	0/80	0/80	0/80	0/80
					96 Hrs	0/80	0/80	0/80	0/80
	H3TRB - PC	High Temperature High Humidity Reverse Bias + Preconditioning	Ta=85C, RH = 85% 80% bias or 100V max	c = 0, Room	Post PC Electrical	0/80	0/80	0/80	0/80
					504 Hrs	0/80	0/80	0/80	0/80
					1008 hrs	0/80	0/80	0/80	0/80
	HTSL	High Temp Storage Life	Ta=150°	Cc=0, Room	Initial	0/80	0/80	0/80	0/80
					504 hrs	0/80	0/80	0/80	0/80
					1008Hrs	0/80	0/80	0/80	0/80
	RSH	Resistance to Solder Heat	Tdwell=10 sec @ 260°C	N/A		0/30	0/30	0/30	0/30
	SAT	Scanning Acoustic Analysis	Compare for Delamination pre and post preconditioning	Compare to existing data		0/5	0/5	0/5	0/5
	DPA	Destructive Physical Analysis	Following TC + PC	Compare to AEC Criteria		0/2	0/2	0/2	0/2
	DPA	Destructive Physical Analysis	Following HAST+ PC	Compare to AEC Criteria		0/2	0/2	0/2	0/2

Table 1: Reliability Evaluation Results for Device NUP4302MR6T1G



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ELECTRICAL CHARACTERISTIC SUMMARY:

No changes in device functionality. Device parameters will continue to meet all data sheet specifications.

CHANGED PART IDENTIFICATION: NA

List of affected General Parts:

ASM3P2863AF-06OR